★ Super Low Gate Charge
★ Green Device Available
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Green

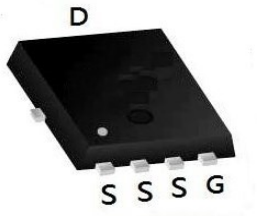
Product Summary

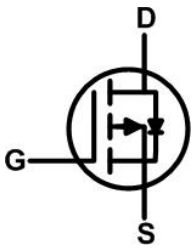
BVDSS	RDSON	ID
-18V	3.6mΩ	-70A

Description

The XXW20P70DF is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.
The XXW20P70DF meet the RoHS and Green Product requirement with full function reliability approved.

PRPAK5x6 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-18	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-70	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-53	A
I_{DM}	Pulsed Drain Current[2]	-280	A
P_D@T_C=25℃	Total Power Dissipation[3]	62	W
P_D@T_C=70℃	Total Power Dissipation[3]	35	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	3	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)		℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]		℃/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-15	18	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -15V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.35	-0.65	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS} =-4.5V, I_D =-15A	-	3.6	5.5	mΩ
		V_{GS} =-2.5V, I_D =-12A	-	4.5	92	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =-10V, V_{GS} =0V, f = 1.0MHz	-	6600	-	pF
C_{oss}	Output Capacitance		-	460	-	pF
C_{rss}	Reverse Transfer Capacitance		-	659	-	pF
Q_g	Total Gate Charge	V_{DS} =-10V, I_D =-15A, V_{GS} =-4.5V	-	76	-	nC
Q_{gs}	Gate-Source Charge		-	10	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	20	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} =-10V, I_D =-13A, R_{GEN}=2.7Ω,V_{GS} =-10V	-	14	-	ns
t_r	Turn-on Rise Time		-	130	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	187	-	ns
t_f	Turn-off Fall Time		-	190	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-70	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-280	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S =-30A	-	-	-1.2	V
trr	Reverse Recovery Time	T_J=25℃,I_{SD}=-15A, V_{GS}=0V di/dt=-100A/μs	-	23	-	ns
Qrr	Reverse Recovery Charge		-	14	-	Nc

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃,V_{DD}=-10V,V_G=-10V, R_G=5.9Ω, L=0.5mh,I_{AS}=-16A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

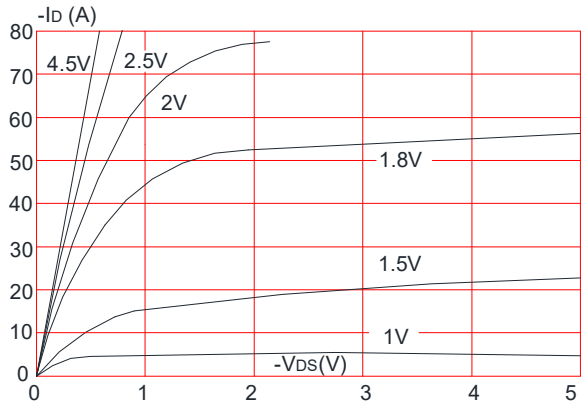


Figure 2: Typical Transfer Characteristics

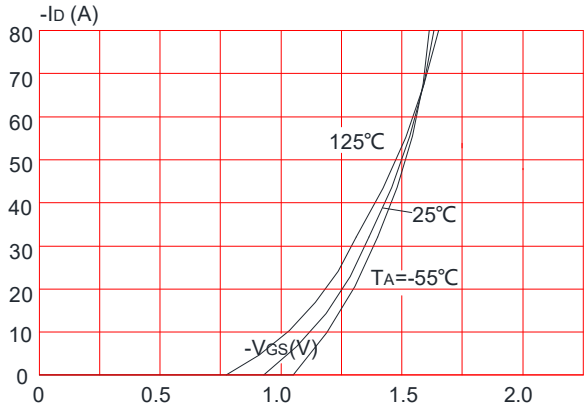


Figure 3: On-resistance vs. Drain Current

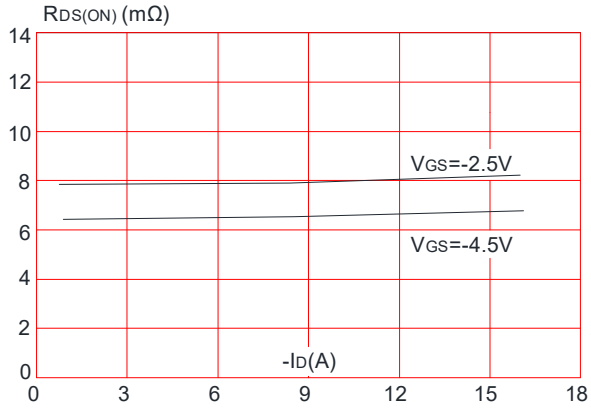


Figure 4: Body Diode Characteristics

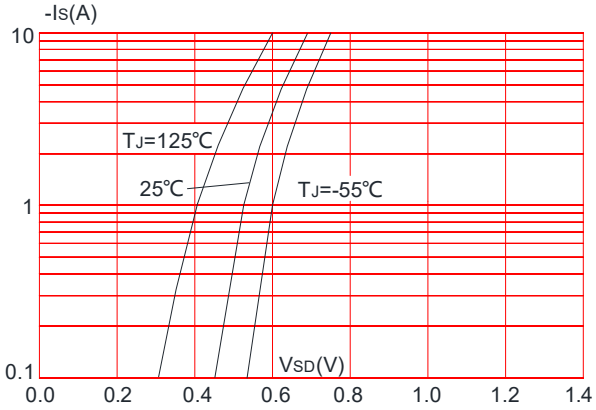


Figure 5: Gate Charge Characteristics

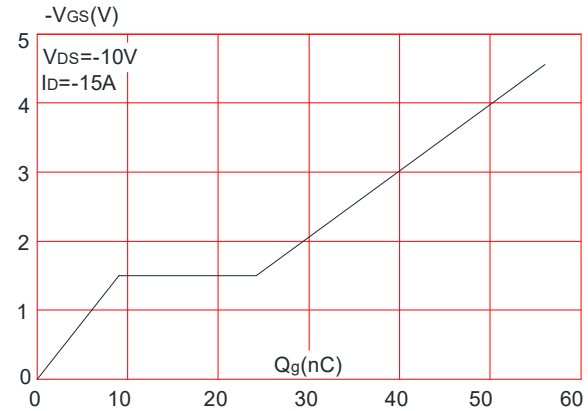


Figure 6: Capacitance Characteristics

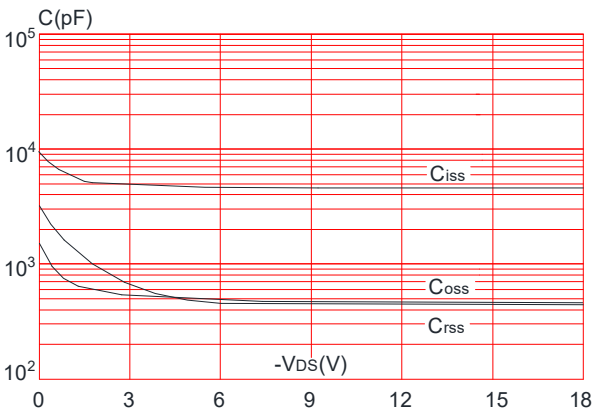


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

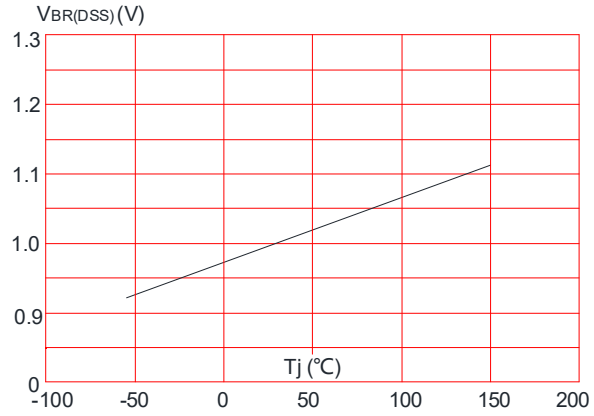


Figure 8: Normalized on Resistance vs. Junction Temperature

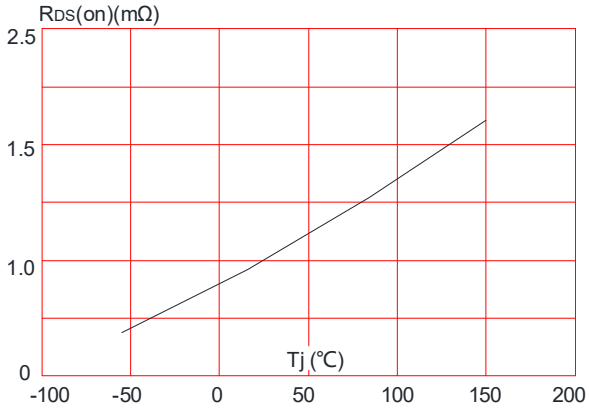


Figure 9: Maximum Safe Operating Area

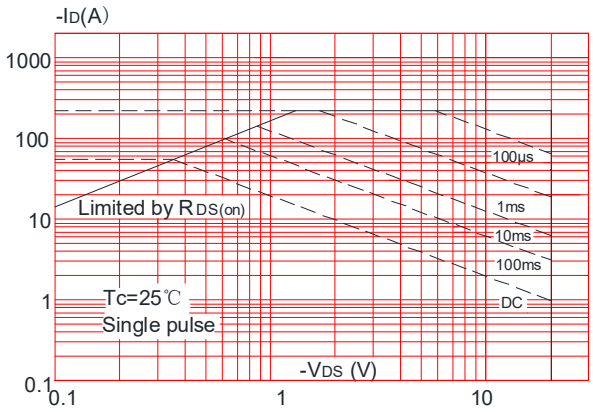


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

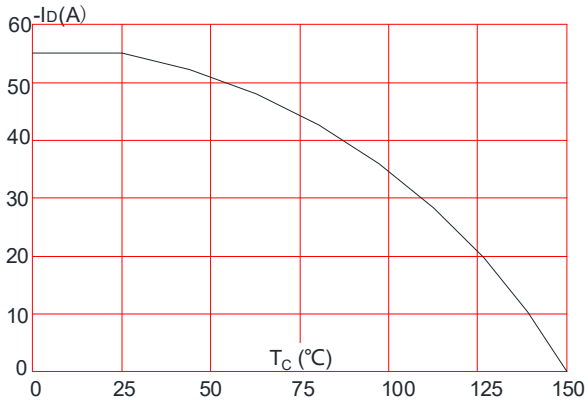
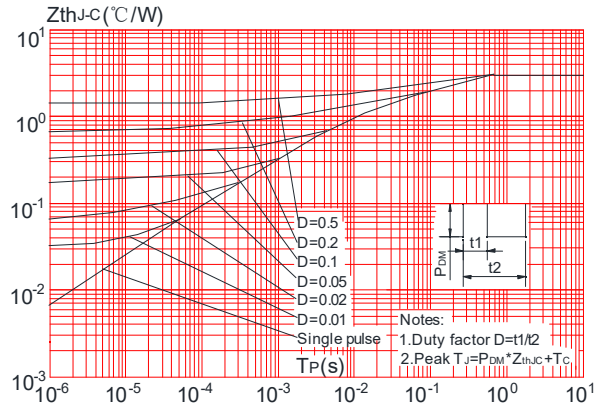
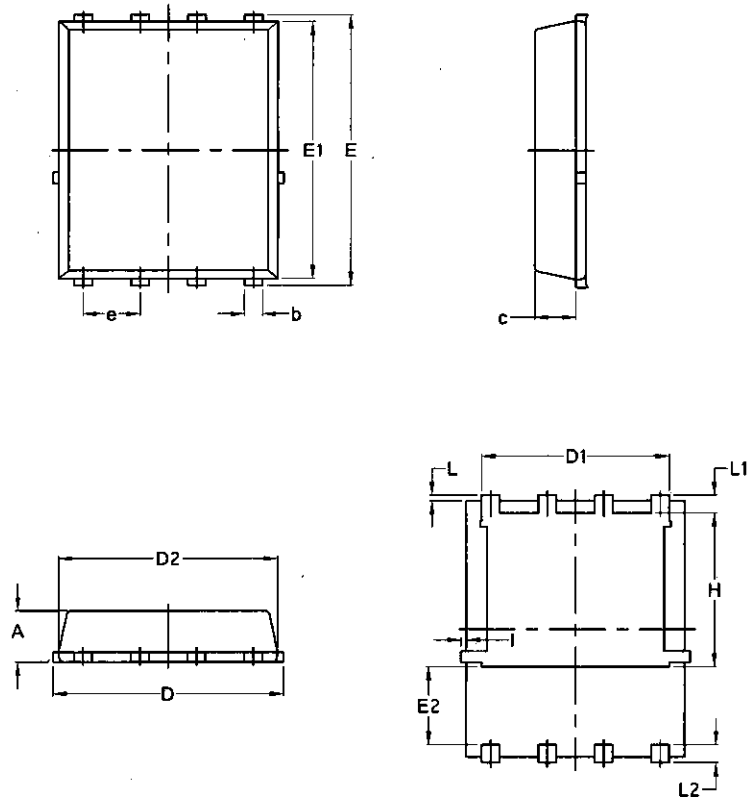


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Package Mechanical Data-DFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070